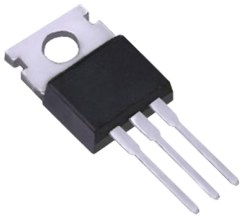
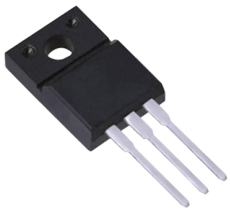
6.2A, 650V N-CHANNEL POWER MOSFET



TO-220



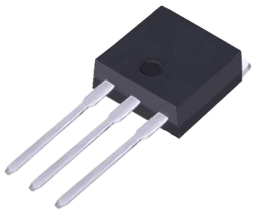
TO-220F

■ DESCRIPTION

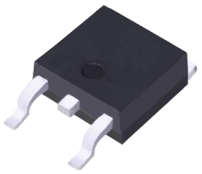
The UTC **6N65** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

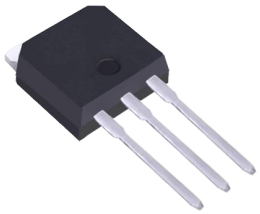
* $R_{DS(ON)}$ < 1.7Ω @V_{GS} = 10V
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness



TO-262



TO-263



TO-251

TO-252

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Avalanche Current (Note 2)		I_{AR}	6.2	A
Continuous Drain Current		I_D	6.2	A
Pulsed Drain Current (Note 2)		I_{DM}	24.8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	440	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F/TO-220F1 TO-220F3		40	W
	TO-220F2		42	W
	TO-251/TO-251S TO-252		55	W
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J
3. L = 24mH, I_{AS} = 6A, V_{DD} = 90V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 6.2A, di/dt ≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	θ_{JA}	62.5	°C/W
	TO-251/TO-251S TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.0	°C/W
	TO-220F/TO-220F1 TO-220F3		3.2	
	TO-220F2		2.97	
	TO-251/TO-251S TO-252		2.27	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 650V, V_{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA, Referenced to 25°C		0.53		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10V, I_D = 3.1A		1.1	1.7	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0 MHz		950	1200	pF
Output Capacitance		C_{OSS}			95	120	pF
Reverse Transfer Capacitance		C_{RSS}			18	25	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	V_{DD}=325V, I_D =6.2A, R_G =25Ω (Note 1, 2)		45	60	ns
Turn-On Rise Time		t_R			100	130	ns
Turn-Off Delay Time		$t_{D(OFF)}$			300	400	ns
Turn-Off Fall Time		t_F			220	270	ns
Total Gate Charge		Q_G	V_{DS}=520V, I_D=6.2A, V_{GS}=10V (Note 1, 2)		180	200	nC
Gate-Source Charge		Q_{GS}			8		nC
Gate-Drain Charge		Q_{GD}			20		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 6.2 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				6.2	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				24.8	A
Reverse Recovery Time		t_{RR}	V_{GS} = 0 V, I_S = 6.2 A, dI_F/dt = 100 A/μs (Note 1)		290		ns
Reverse Recovery Charge		Q_{RR}			2.35		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS